InAlGaN superluminescent diodes fabricated on patterned substrates: an alternative semiconductor broadband emitter: publisher’s note

Anna Kafar,1,* Szymon Stanczyk,1 Marcin Sarzynski,1 Szymon Grzanka,1,2 Jakub Goss,1 Irina Makarowa,2 Anna Nowakowska-Siwinska,2 Tadek Suski,1 and Piotr Perlin1,2

1Institute of High Pressure Physics, Polish Academy of Sciences, Sokolowska 29/37, 01-142 Warsaw, Poland
2TopGaN Ltd., Sokolowska 29/37, 01-142 Warsaw, Poland
*Corresponding author: ak@unipress.waw.pl

Received 24 April 2018; posted 24 April 2018 (Doc. ID 330275); published 24 May 2018

This publisher’s note reports the revision of the funding section in Photon. Res. 5, A30 (2017).


It is revised with a grant No. “2013/11/N/ST7/02714” added. The Funding Section should be as follows: Narodowe Centrum Nauki (NCN) (2013/11/N/ST7/02714, 2014/15/B/ST3/04252); Narodowe Centrum Badań Rozwoju (NCBR) (1/POLBER-1/2014).

The article [1] was corrected online as of 17 May 2018.

REFERENCE